

**DESCRIPTION**

M57915L is a Hybrid Integrated Circuit designed for driving Transistor Modules QM10XX, QM20XX, etc., in an Inverter application. This device operates as an isolation amplifier for Transistor Modules due to the electrical isolation between the input and output circuits with a opto-coupler, as well as its driving capability which only requires single power supply.

**FEATURES**

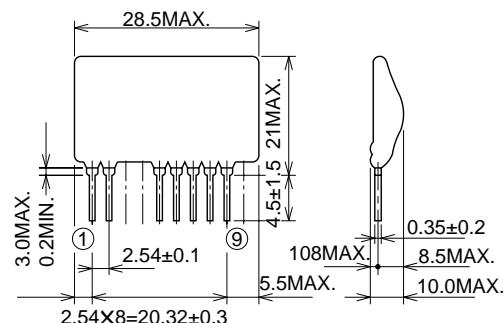
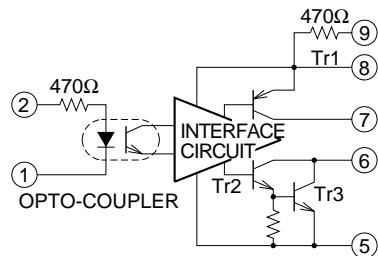
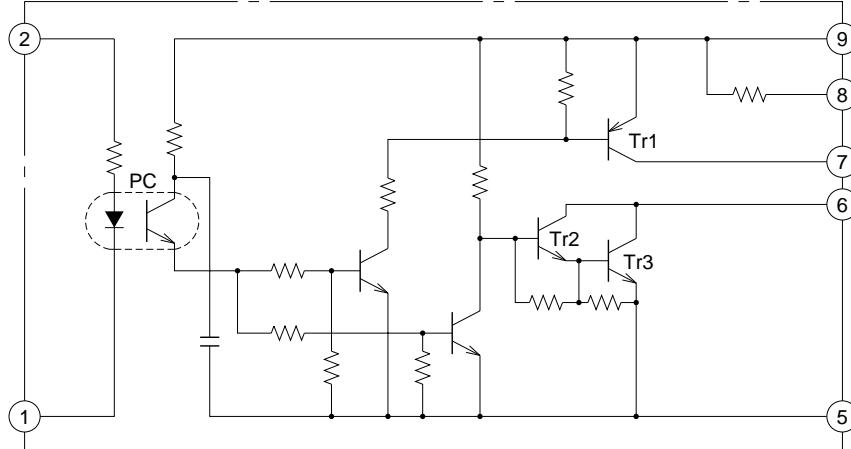
- Electrical isolation between input and output with integrated opto-coupler.  $V_{iso}=2500\text{Vrms}$
- Applicable with single power supply (7 ~ 9V)
- Applicable with TTL input

**APPLICATION**

To drive Transistor Modules for Inverter applications

**OUTLINE DRAWING**

Dimensions in mm

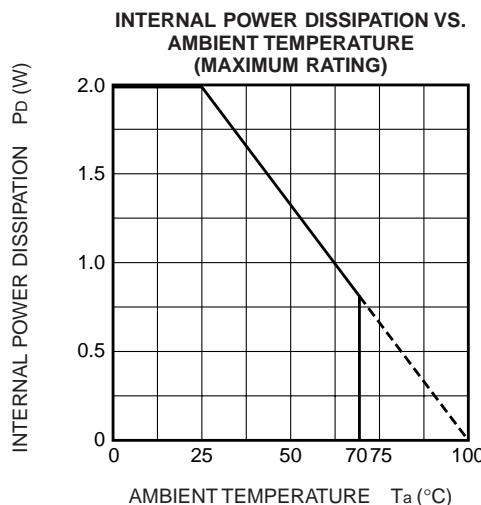
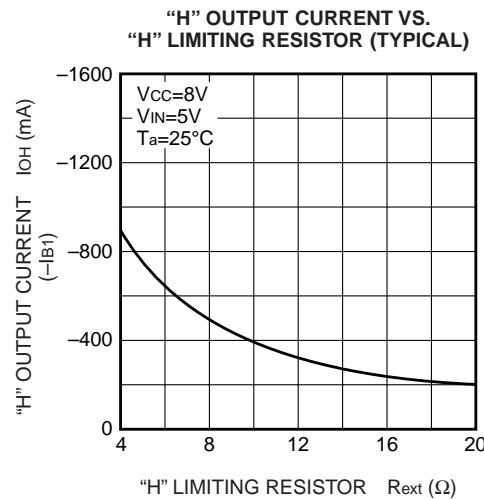
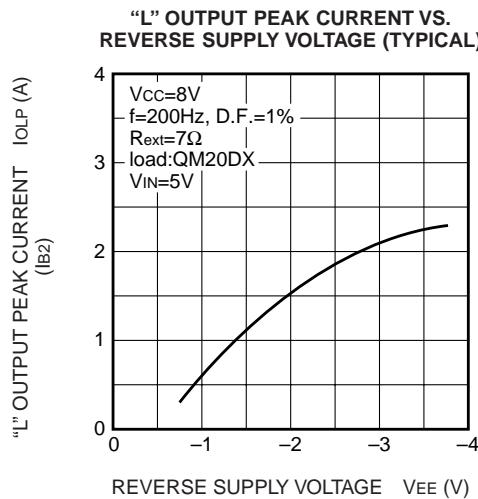
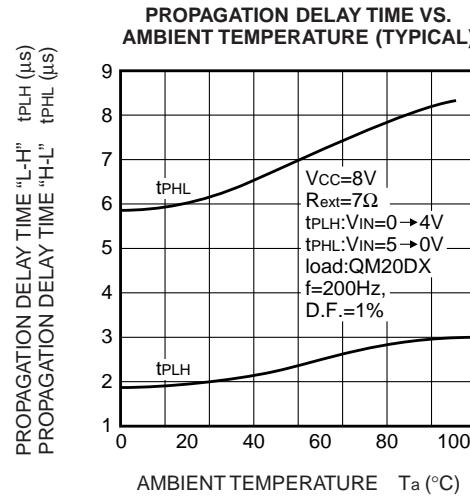
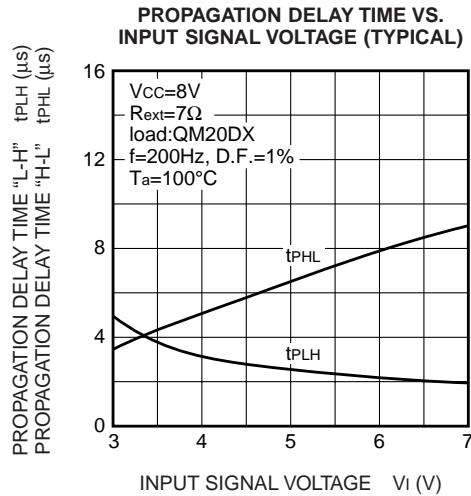
**BLOCK DIAGRAM****CIRCUIT DIAGRAM**

**HYBRID IC FOR DRIVING TRANSISTOR MODULES****ABSOLUTE MAXIMUM RATINGS** ( $T_a=-20 \sim +70^\circ\text{C}$ , unless otherwise noted)

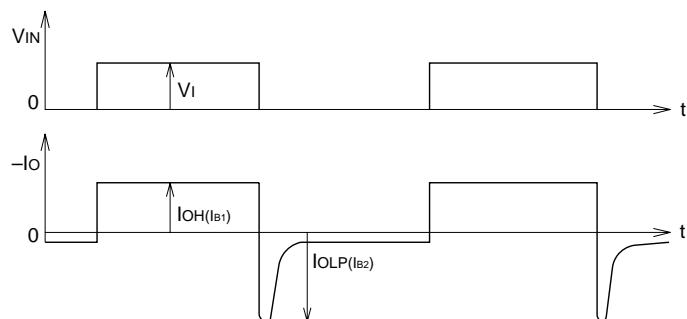
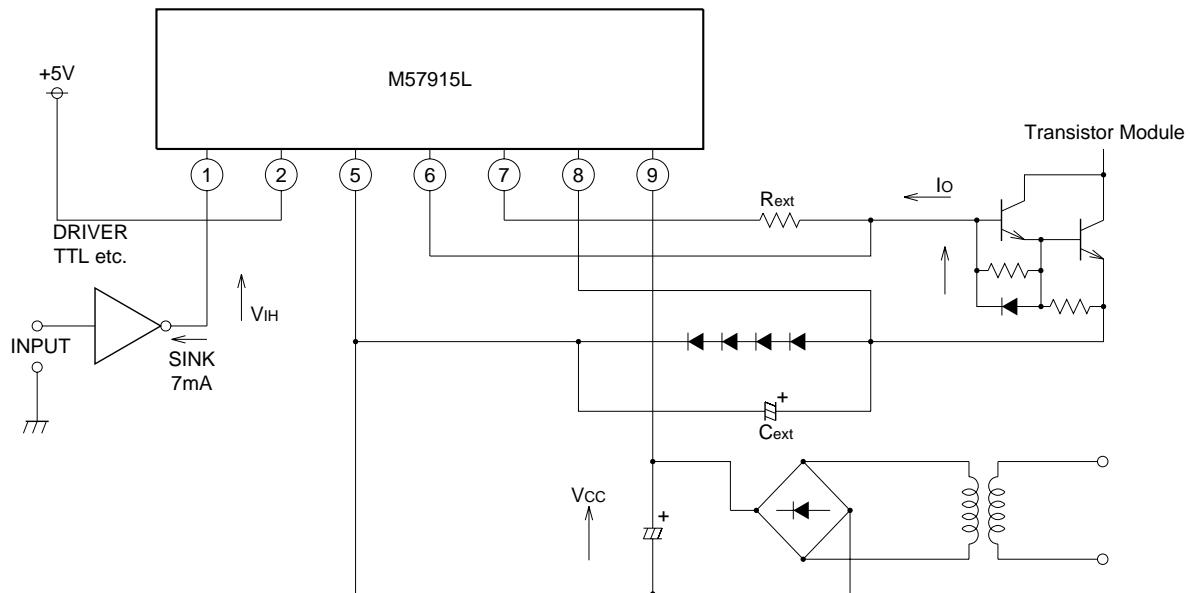
Symbol	Parameter	Conditions	Ratings	Unit
Vcc	Supply voltage	DC	14	V
Vi	Input voltage	Between terminals ① and ②	-1 ~ 7	V
IOH			-1	A
IOLP	Output current	Pulse width 10μs, Freq. 2kHz, peak value	3	A
Viso	Isolation voltage	Sinewave voltage 60Hz/min. $T_a=25^\circ\text{C}$	2500	Vrms
Tj	Junction temperature		100	°C
Topg	Operating temperature		-20 ~ +70	°C
Tstg	Storage temperature		-25 ~ +100	°C

**ELECTRICAL CHARACTERISTICS** ( $T_a=25^\circ\text{C}$ ,  $Vcc=8\text{V}$ , unless otherwise noted)

Symbol	Parameter	Test conditions	Limits			Unit
			Min.	Typ.	Max.	
IIH	"H" input current	Vi=5V	-	7	-	mA
IOH	"H" output current	Rext=7Ω	-	-0.5	-	A
IOLP	"L" output peak current	Cext=47μF	-	1	-	A
PD	Internal power dissipation	IOH=-0.5A, IOLP=1A, f=2kHz, D.F.=50%	-	0.8	-	W
tPLH	"L-H" propagation delay time	Vi=0→4V, Tj=100°C	-	5	10	μs
tPHL	"H-L" propagation delay time	Vi=5→0V, Tj=100°C	-	8	15	μs

**PERFORMANCE CURVES**

## TEST CIRCUIT AND APPLICATION CIRCUIT EXAMPLE



**Note:**  $I_{OH}$  and  $I_{OLP}$  correspond to base forward current  $I_{B1}$  and base reverse current  $I_{B2}$  of the transistor module to be driven respectively.